

IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the above-referenced application.

1-10. (Cancelled).

11. (Previously Presented) A light-emitting semiconductor device comprising:
a semiconductor structure having at least one p-type and one n-type layer; and
a p contact and an n contact, the p contact electrically connected to the p-type layer,
the n contact electrically connected to the n-type layer, wherein at least one of the p and n
contacts is a multi-layer contact external to the semiconductor structure, the multi-layer
contact comprising:

a metallic reflector layer comprising Ag; and

a continuous uniform conducting sheet adjacent to the semiconductor structure,
wherein the continuous uniform conducting sheet comprises Ni and makes ohmic
contact to the structure;

wherein the multi-layer contact has a reflectivity greater than 75% for light at an
operating wavelength of the light-emitting device and a specific contact resistance less than
 $10^{-2} \Omega\text{-cm}^2$.

12-13. (Cancelled).

14. (Previously Presented) A device, as defined in claim 11, the multi-layer contact
further comprising a barrier layer interposing the reflector layer and the continuous uniform
conducting sheet.

15. (Original) A device, as defined in claim 11, the reflector layer having a
thickness greater than 500 Å.

16. (Previously Presented) A device, as defined in claim 11, wherein the
continuous uniform conducting sheet has a thickness less than 200 Å.

17. (Canceled).
18. (Previously Presented) A device, as defined in claim 11, wherein the continuous uniform conducting sheet is selected from the group that consists of Au/NiO and Ni/Au.
19. (Canceled).
20. (Previously Presented) A device, as defined in claim 11, wherein the semiconductor structure includes at least one III-nitride layer.
- 21-27. (Canceled).
28. (Previously Presented) A device, as defined in claim 11, wherein the continuous uniform conducting sheet absorbs less than 25% of light generated in the semiconductor structure and incident on the continuous uniform conducting sheet.
29. (Previously Presented) A device, as defined in claim 20, wherein a voltage required to forward bias the device is less than 3.5 V.
30. (Previously Presented) A device, as defined in claim 11, wherein the continuous uniform conducting sheet has thickness less than 100 Å.
31. (Previously Presented) A light-emitting semiconductor device comprising:
a semiconductor structure having at least one p-type and one n-type layer; and
a p contact and an n contact, the p contact electrically connected to the p-type layer, the n contact electrically connected to the n-type layer, wherein at least one of the p and n contacts is a multi-layer contact external to the semiconductor structure, the multi-layer contact comprising:
a metallic reflector comprising Al; and
a continuous uniform conducting sheet adjacent to the semiconductor structure, wherein the continuous uniform conducting sheet comprises Ni and makes ohmic contact to the structure;

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wherein the multi-layer contact has a reflectivity greater than 75% for light at an operating wavelength of the light-emitting device and a specific contact resistance less than $10^{-2} \Omega\text{-cm}^2$.

32-34. (Canceled).

35. (Previously Presented) A device, as defined in claim 31, wherein: the continuous uniform conducting sheet comprises Au.

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